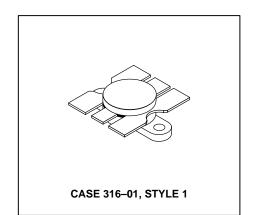
The RF Line NPN Silicon RF Power Transistor

... designed for 12.5 Volt UHF large—signal amplifier applications in industrial and commercial FM equipment operating to 512 MHz.

- Specified 12.5 Volt, 470 MHz Characteristics —
 Output Power = 15 Watts
 Minimum Gain = 7.8 dB
 Efficiency = 55%
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Built-In Matching Network for Broadband Operation
- Tested for Load Mismatch Stress at all Phase Angles with 20:1 VSWR @ 16-Volt High Line and Overdrive
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF641

15 W, 470 MHz CONTROLLED Q RF POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	16	Vdc
Collector–Base Voltage	VCBO	36	Vdc
Emitter-Base Voltage	VEBO	4.0	Vdc
Collector Current — Continuous	IC	3.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	43.7 0.25	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.0	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, I _B = 0)	V(BR)CEO	16	_	_	Vdc
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, V _{BE} = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 5.0 mAdc, I _C = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V _{CE} = 15 Vdc, V _{BE} = 0, T _C = 25°C)	ICES	_	_	5.0	mAdc

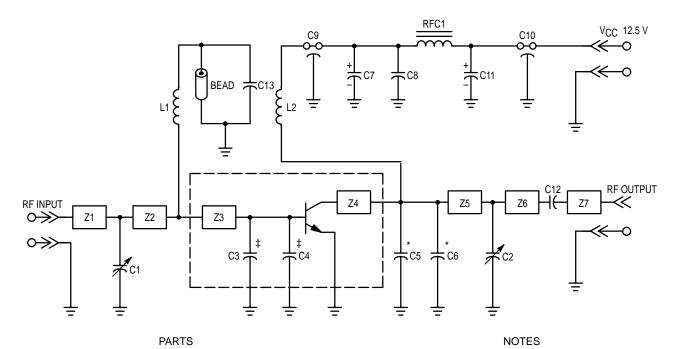
(continued)

REV 6



ELECTRICAL CHARACTERISTICS — **continued** $(T_C = 25^{\circ}C)$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (IC = 1.0 Adc, VCE = 5.0 Vdc)	hFE	30	70	150	_
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 12.5 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	40	60	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (V _{CC} = 12.5 Vdc, P _{Out} = 15 W, f = 470 MHz)	G _{pe}	7.8	8.5	_	dB
Collector Efficiency (V _{CC} = 12.5 Vdc, P _{Out} = 15 W, f = 470 MHz)	η	55	60	_	%
Output Mismatch Stress (V _{CC} = 16 Vdc, P _{in} = 3.0 W, f = 470 MHz, VSWR = 20:1, All Phase Angles)	Ψ	No Degradation in Output Power			



Z1 — 1.225" x 0.187" Microstrip Z2 — 0.884" x 0.187" Microstrip

Z3 — Capacitor Block (Base) Z4 — Collector Block

Z5 — 1.1" x 0.187" Microstrip

Z6 — 0.433" x 0.187" Microstrip

Z7 — 0.4" x 0.187" Microstrip

Dotted Area — Capacitor Assembly

C1, C2 — 0.8-10 pF Johanson

C3, C4 — 24 pF Chip Caps 100 mils ATC

C5, C6 — 22 pF Chip Caps 100 mils ATC

C12 — 220 pF Chip Cap 100 mils ATC

C7, C11 — 1.0 μF Tantalum 35 Vdc

C9, C10 — 680 pF Feedthrough Allen-Bradley

C13 — 200 pF UNELCO

 $C8 - 0.1 \mu F$, 50 V Erie Red Cap

RFC1 — VK 200 — 104B Ferrite Choke

L1 — 4 Turns 0.2" Dia. #16 AWG

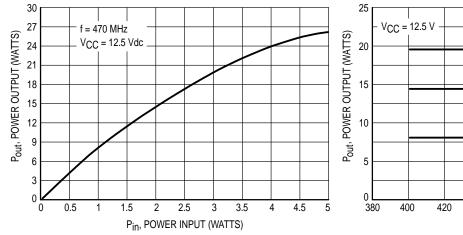
L2 - 9 Turns 0.15" Dia. #16 AWG

Bead — Ferroxcube 56-590-65-35EB

*C5, C6, are mounted as close to the capacitor assembly as possible.

‡‡C3, C4 are mounted in the capacitor assembly. Board — 62.5 mil Glass Teflon, ϵ_{r} = 2.55.

Figure 1. Test Circuit Schematic



25 V_{CC} = 12.5 V P_{in} = 3 W

10 2 W

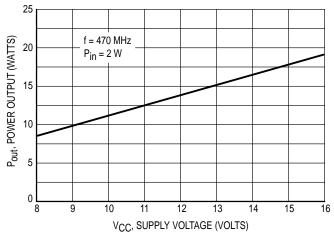
10 1 W

380 400 420 440 460 480 500 520 540

f, FREQUENCY (MHz)

Figure 2. Power Output versus Power Input

Figure 3. Power Output versus Frequency



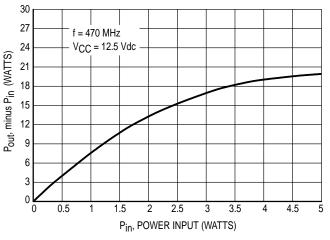
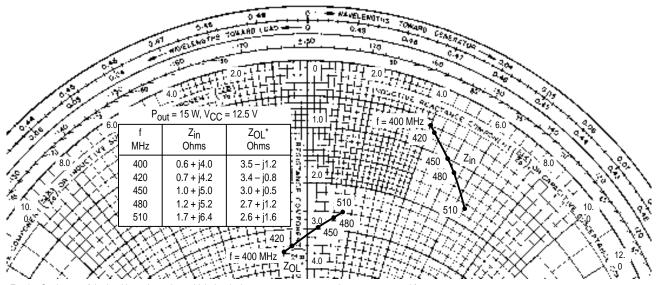


Figure 4. Power Output versus Supply Voltage

Figure 5. Power Saturation Profile

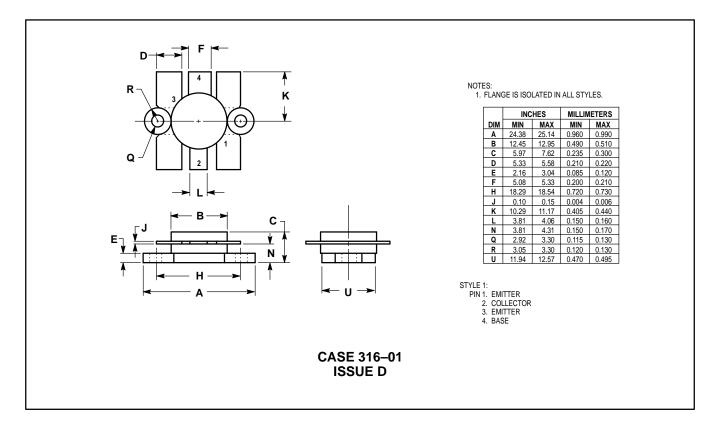


 $Z_{OL}{}^{\star} = \text{Conjugate of the load impedance into which the device output operates at a given power, } \eta, \text{ and frequency.}$

Figure 6. Series Equivalent Input-Output Impedance

MOTOROLA RF DEVICE DATA MRF641

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